

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Canceled).

Claim 6 (Currently Amended): A semiconductor device comprising:

a semiconductor substrate;

an inductor provided with a first conductor interconnection formed spirally on ~~[[a]]~~  
the semiconductor substrate; and

a shield that is provided with a second conductor interconnection in a ring having a continuous configuration provided along an outer periphery of the spiral pattern of the inductor ~~[[with]]~~ except for an opening in a portion of the second conductor interconnection, and ~~[[that]]~~ the second conductor is electrically connected to ground potential, wherein  
said shield includes a plurality of components with the plural components extending in corresponding plural planes.

Claim 7 (Previously Presented): A semiconductor device according to Claim 6, wherein an interconnection width of the shield is equal to or more than a size of a spacing of the spiral pattern of the inductor, and is equal to or less than a radius of the spiral pattern of the inductor.

Claim 8 (Previously Presented): A semiconductor device according to Claim 6, wherein a distance between the shield and an outer border of the interconnection of the inductor is equal to a spacing of the spiral pattern of the inductor.

Claim 9 (Previously Presented): A semiconductor device according to Claim 6, further comprising:

a plurality of interconnection layers formed on the semiconductor substrate, wherein the inductor is formed in any one of these interconnection layers; and the shield is formed in a different interconnection layer from the interconnection layer in which the inductor is formed.

Claim 10 (Currently Amended): A semiconductor device comprising:

a semiconductor substrate;

an inductor provided with a first conductor interconnection formed spirally on [[a]] the semiconductor substrate; and

a shield that is provided with a second conductor interconnection in a ring having a continuous configuration provided along an inner periphery of the spiral pattern of the inductor [[with]] except for an opening in a portion of the second conductor interconnection, and [[that]] the second conductor is electrically connected to ground potential, wherein

said shield includes a plurality of components with the plural components extending in corresponding plural planes.

Claim 11 (Previously Presented): A semiconductor device according to Claim 10, wherein an interconnection width of the shield is equal to or less than a size of an interconnection width of the inductor.

Claim 12 (New): The semiconductor device according to Claim 6, wherein

the plural components of the shield include a first and second component each having a perimeter that is partially opened, and

the first and second components are arranged such that the openings in the perimeters of the first and second components are not superposed in a stacked state of the plural components.